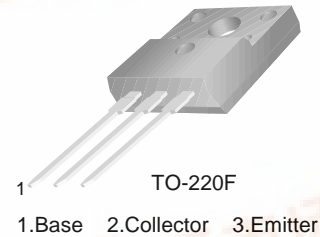




## KSE13007F

### High Voltage Switch Mode Application

- High Speed Switching
- Suitable for Switching Regulator and Motor Control



### NPN Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector- Base Voltage	700	V
$V_{CEO}$	Collector- Emitter Voltage	400	V
$V_{EBO}$	Emitter- Base Voltage	9	V
$I_C$	Collector Current (DC)	8	A
$I_{CP}$	Collector Current (Pulse)	16	A
$I_B$	Base Current	4	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CEO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{mA}, I_B = 0$	400			V
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			1	mA
$h_{FE}$	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 2\text{A}$ $V_{CE} = 5\text{V}, I_C = 5\text{A}$	8 5		60 30	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}$ $I_C = 8\text{A}, I_B = 2\text{A}$			1 2 3	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$ $I_C = 5\text{A}, I_B = 1\text{A}$			1.2 1.6	V V
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}, f = 0.1\text{MHz}$		110		pF
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	4			MHz
$t_{ON}$	Turn On Time	$V_{CC} = 125\text{V}, I_C = 5\text{A}$			1.6	$\mu\text{s}$
$t_{STG}$	Storage Time	$I_{B1} = - I_{B2} = 1\text{A}$			3	$\mu\text{s}$
$t_F$	Fall Time	$R_L = 50\Omega$			0.7	$\mu\text{s}$

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

# Typical Characteristics

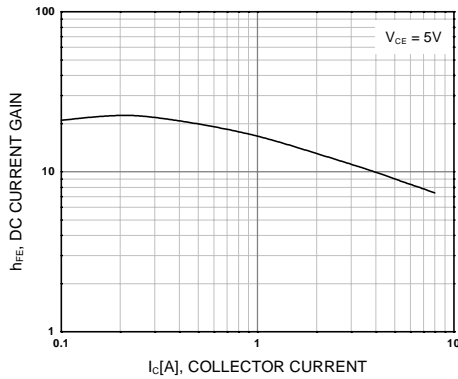


Figure 1. DC current Gain

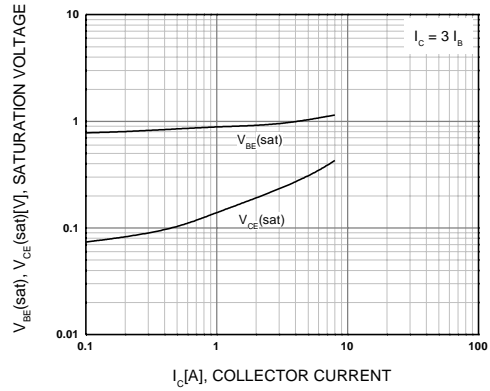


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

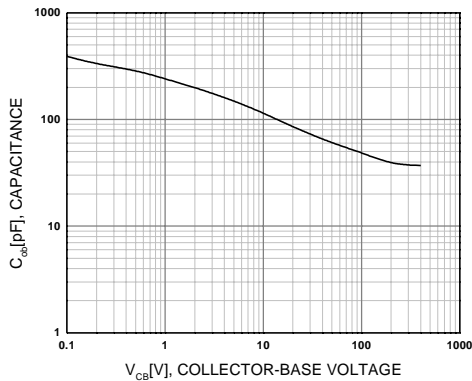


Figure 3. Collector Output Capacitance

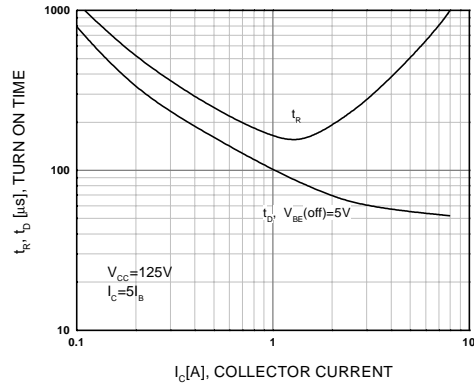


Figure 4. Turn On Time

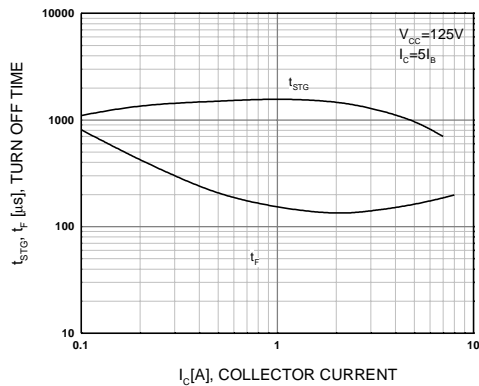


Figure 5. Turn Off Time

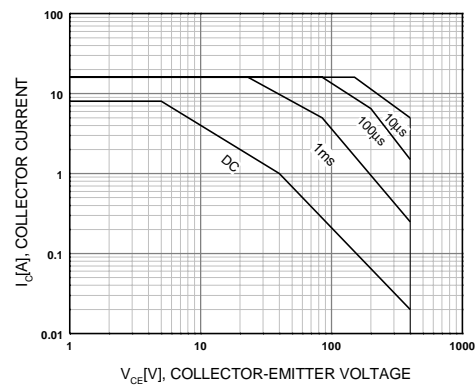


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

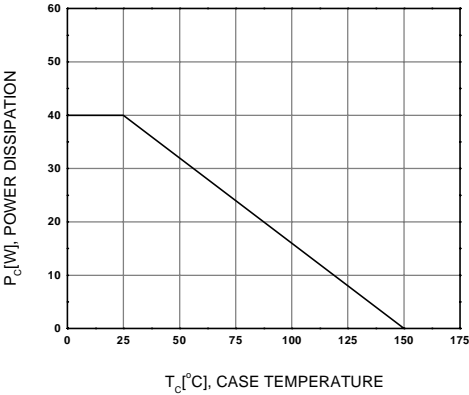


Figure 7. Power Derating

Technical drawing of a probe head assembly, showing three views: front, side, and bottom views. The drawing includes the following dimensions and specifications:

- Front View:**
  - Overall width:  $10.16 \pm 0.20$
  - Distance between mounting holes:  $(7.00)$
  - Mounting hole diameter:  $\varnothing 3.18 \pm 0.10$
  - Top flange thickness:  $3.30 \pm 0.10$
  - Main body height:  $15.80 \pm 0.20$
  - Probe body diameter:  $0.80 \pm 0.10$
  - Probe body length:  $9.75 \pm 0.30$
  - Probe tip diameter:  $0.35 \pm 0.10$
  - Probe tip angle:  $(30^\circ)$
  - Probe tip material:  $\#1$
  - Probe body material:  $2.54\text{TYP}$  [ $2.54 \pm 0.20$ ]
- Side View:**
  - Top flange thickness:  $2.54 \pm 0.20$
  - Top flange width:  $(0.70)$
  - Probe body diameter:  $6.68 \pm 0.20$
  - Probe body length:  $15.87 \pm 0.20$
  - Probe body material:  $2.76 \pm 0.20$
  - Probe body diameter:  $0.50^{+0.10}_{-0.05}$
  - Probe body angle:  $(1.00 \times 45^\circ)$
- Bottom View:**
  - Overall width:  $9.40 \pm 0.20$
  - Overall height:  $4.70 \pm 0.20$

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DOME™	HiSeC™	Power247™	SuperSOT™-6	
EcoSPARK™	I <sup>2</sup> C™	PowerTrench®	SuperSOT™-8	
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